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Band-gap reference voltage source

Inventor(s): ANNEMA ANNE J [NL] ± (ANNEMA, ANNE J)

Applicant(s): PHILIPS CORP [US] ± (U.S. PHILIPS CORPORATION)

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Abstract of US5942887 (A)

A band-gap reference voltage source comprises a first current branch including a first field effect transistor (T1); a second current branch including a second field effect transistor (T2); a reference resistor (RRF) arranged in series with one of the field effect transistors (T1, T2); and a voltage level shifter for coupling the backgates (BG1, BG2) of the field effect transistors (T1, T2) to the gates (G1, G2) of the field effect transistors (T1, T2), which reduces the gate-source voltages of the field effect transistors (T1, T2). As a result of this, the output voltage supplied by the band-gap reference voltage source can be lower than customary.

